

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



November 2012

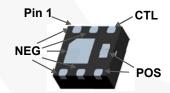
FR011L5J (11m Ω , -30V) Low-Side Reverse Bias / Reverse Polarity Protector

Features

- Up to -30V Reverse-Bias Protection
- Nano Seconds of Reverse-Bias Blocking Response Time
- +29V 24-Hour "Withstand" Rating
- 11mΩ Typical Series Resistance at 5V
- MicroFET™ 2x2mm Package Size
- RoHs Compliant
- USB Tested and Compatible

Applications

- USB 1.0, 2.0 and 3.0 Devices
- USB Charging
- Mobile Devices
- Mobile Medical
- POS Systems
- Toys
- Any DC Barrel Jack Powered Device
- Any DC Devices subject to Negative Hot Plug or Inductive Transients
- Automotive Peripherals



MicroFET2x2 mm

Description

Reverse bias is an increasingly common fault event that may be generated by user error, improperly installed batteries, automotive environments, erroneous connections to third-party chargers, negative "hot plug" transients, inductive transients, and readily available negatively biased rouge USB chargers.

Fairchild circuit protection is proud to offer a new type of reverse bias protection devices. The FR devices are low resistance, series switches that, in the event of a reverse bias condition, shut off power and block the negative voltage to help protect downstream circuits.

The FR devices are optimized for the application to offer best in class reverse bias protection and voltage capabilities while minimizing size, series voltage drop, and normal operating power consumption.

In the event of a reverse bias application, FR011L5J devices effectively provide a full voltage block and can easily protect -0.3V rated silicon.

From a power perspective, in normal bias, an $11m\Omega$ FR device in a 1.5A application will generate only 17mV of voltage drop or 25mW of power loss. In reverse bias, FR devices dissipate less then $20\mu W$ in a 16V reverse bias event. This type of performance is not possible with a diode solution.

Benefits extend beyond the device. Due to low power dissipation, not only is the device small, but heat sinking requirements and cost can be minimized as well.

Ordering Information

Part Number	Top Mark	Package	Packing Method
FR011L5J	11L	6-Lead, Molded Leadless Package (MLP), Dual, Non-JEDEC, 2mm Square, Single-Tied DAP	3000 on Tape & Reel; 7-inch Reel, 12mm Tape

Diagrams

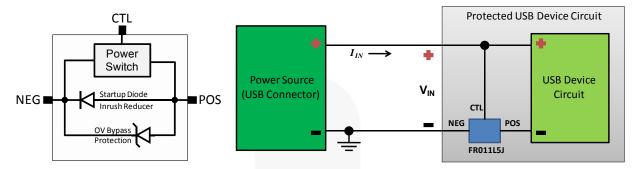


Figure 1. Block Diagram

Figure 2. Typical Schematic

Pin Configuration

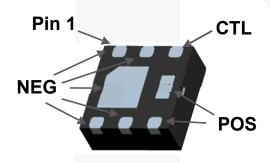


Figure 3. Pin Assignments

Pin Definitions

Name	Pin	Description
POS	4	The ground of the load circuit being protected. Current flows into this pin during normal operation.
CTL	3	The control pin of the device. A positive voltage to the NEG pin turns the switch on and a negative voltage turns the switch to a high-impedance state.
NEG	1, 2, 5, 6	The ground of the input power source. Current flows out of this pin during normal operation.

Absolute Maximum Ratings

Values are at T_A=25°C unless otherwise noted.

Symbol	Parameter		Value	Unit	
V+ _{MAX_OP}	Steady-State Normal Operating Voltage between CTL and NEG Pins (V _{IN} = V+ _{MAX_OP} , I _{IN} = 1.5A, Switch On)		+20		
V+ ₂₄	24-Hour Normal Operating Voltage Withstand Capability between CTL and NEG Pins (V _{IN} = V+ ₂₄ , I _{IN} = 1.5A, Switch On)		+29	V	
V- MAX_OP	Steady-State Reverse Bias Standoff Voltage between CTL and NEG Pins $(V_{IN} = V_{MAX_OP})$		-30		
I _{IN}	Input Current	V _{IN} = 5V, Continuous ⁽²⁾ (see Figure	re 4)	10	Α
TJ	Operating Junction Temperature		150	°C	
	Power Dissipation	$T_A = 25^{\circ}C^{(2)}$ (see Figure 4)		2.4	W
P _D		$T_A = 25^{\circ}C^{(2)}$ (see Figure 5)		0.9	VV
I _{DIODE_CONT}	Steady-State Diode Continuous Forward Current from POS to NEG			2	А
I _{DIODE_PULSE}	Pulsed Diode Forward Current from POS to NEG (300µs Pulse)			210	A
ESD	Human Body Model, JESD22-A114		0.6		
	Electrostatic Discharge Capability	Charged Device Model, JESD22-C101		2	kV
		System Model, IEC61000-4-2 (CTL is shorted to POS) ⁽³⁾	Contact	8	ΚV
			Air	15	

Notes:

- 1. The V₊₂₄ rating is NOT a survival guarantee. It is a statistically calculated survivability reference point taken on qualification devices, where the predicted failure rate is less than 0.01% at the specified voltage for 24 hours. It is intended to indicate the device's ability to withstand transient events that exceed the recommended operating voltage rating. Specification is based on qualification devices tested using accelerated destructive testing at higher voltages, as well as production pulse testing at the V₊₂₄ level. Production device field life results may vary. Results are also subject to variation based on implementation, environmental considerations, and circuit dynamics. Systems should never be designed with the intent to normally operate at V₊₂₄ levels. Contact Fairchild Semiconductor for additional information.
- The device power dissipation and thermal resistance (R_θ) are characterized with device mounted on the following FR4 printed circuit boards, as shown in Figure 4 and Figure 5
- 3. Conducted with shorted load. Open load performance is not guaranteed.



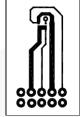


Figure 4. 1 Square Inch of 2-ounce copper

Figure 5. Minimum Pads of 2-ounce Copper

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁽²⁾ (see Figure 4)	61	°C/W
R _{0JA}	Thermal Resistance, Junction to Ambient ⁽²⁾ (see Figure 5)	153	C/VV

Electrical Characteristics

Values are at $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Positive Bia	as Characteristics			•		
	Device Resistance, Switch On	V _{IN} = +4V, I _{IN} = 1.5A		13	20	
		$V_{IN} = +5V$, $I_{IN} = 1.5A$		11	15	mΩ
R _{ON}		$V_{IN} = +5V$, $I_{IN} = 1.5A$, $T_J = 125$ °C		15		
		$V_{IN} = +12V$, $I_{IN} = 1.5A$		9	13	
V_{ON}	Input Voltage, V _{IN} , at which Voltage at POS, V _{POS} , Reaches a Certain Level at Given Current	I _{IN} = 100mA, V _{POS} = 45mV, V _{NEG} = 0V	1.4	2.4	3.5	V
ΔV_{ON} / ΔT_{J}	Temperature Coefficient of V _{ON}			-3.9		mV/°C
I _{DIODE_CONT}	Continuous Diode Forward Current	$V_{CTL} = V_{POS}$			2	Α
V_{F}	Diode Forward Voltage	$V_{CTL} = V_{POS}, I_{DIODE} = 0.1A,$ Pulse width < 300 μ s	0.56	0.60	0.73	V
I _{BIAS}	Bias Current Flowing out of NEG Pin during Normal Bias Operation	V_{CTL} = 5V, V_{NEG} = 0V, No Load		15		nA
Negative Bi	as Characteristics					
V- MAX_OP	Reverse Bias Breakdown Voltage		1		-30	V
Δ V- $_{MAX_OP}$ / Δ T $_{J}$	Reverse Bias Breakdown Voltage Temperature Coefficient	$I_{IN} = -250 \mu A$, $V_{CTL} = V_{POS} = 0 V$		16		mV/°C
l-	Leakage Current from NEG to POS in Reverse-Bias Condition	$V_{NEG} = 20V$, $V_{CTL} = V_{POS} = 0V$		1		μA
t _{RN}	Time to Respond to Negative Bias Condition	V_{NEG} = 5V, V_{CTL} = 0V, C_{LOAD} = 10 μ F, Reverse Bias Startup Inrush Current = 0.2A			50	ns
Dynamic C	haracteristics					
Сι	Input Capacitance between CTL and NEG			1011		
Cs	Switch Capacitance between POS and NEG	$V_{IN} = -5V$, $V_{CTL} = V_{POS} = 0V$, f = 1MHz		81		pF
Co	Output Capacitance between CTL and POS			1456		
R _C	Control Internal Resistance			1.7		Ω

Typical Characteristics

 $T_J = 25$ °C unless otherwise specified.

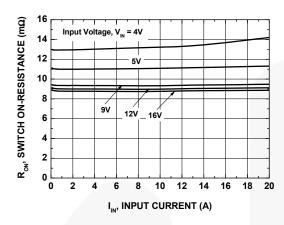
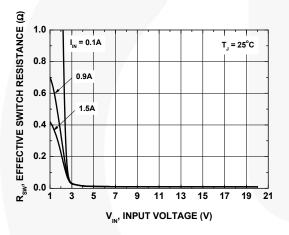


Figure 6. Switch On Resistance vs. Switch Current

Figure 7. Minimum Input Voltage to Turn On Switch vs. Current at 45mV Switch Voltage Drop



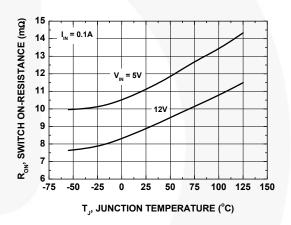
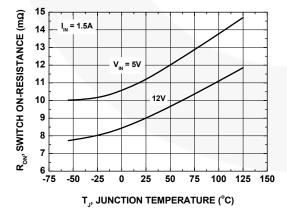


Figure 8. Effective Switch Resistance R_{SW} vs. Input Voltage V_{IN}

Figure 9. Switch On Resistance vs. Junction Temperature at 0.1A



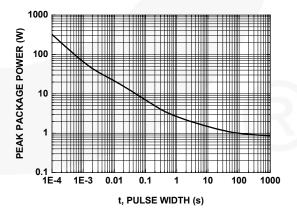


Figure 10. Switch On Resistance vs. Junction Temperature at 1.5A

Figure 11. Single-Pulse Maximum Power vs. Time

Typical Characteristics

 T_J = 25°C unless otherwise specified.

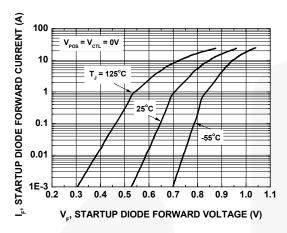


Figure 12. Startup Diode Current vs. Forward Voltage

Application Test Configurations

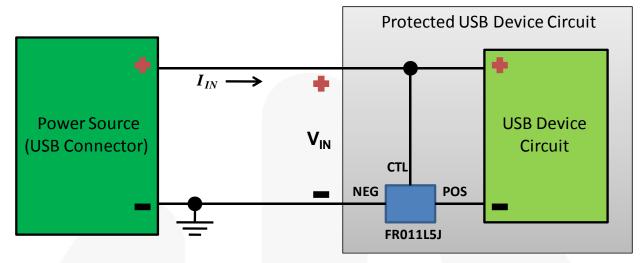


Figure 13. Typical Application Circuit for USB Applications

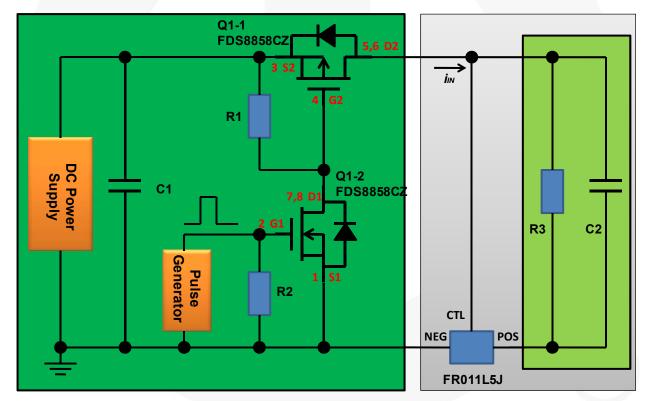


Figure 14. Startup Test Circuit - Normal Bias with FR011L5J

Application Test Configurations (Continued)

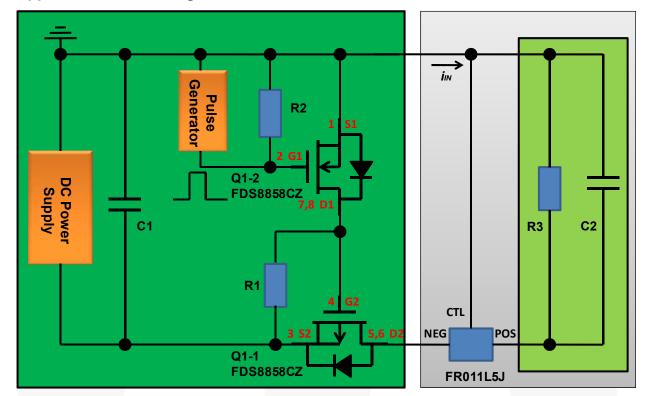


Figure 15. Startup Test Circuit - Reverse Bias with FR011L5J

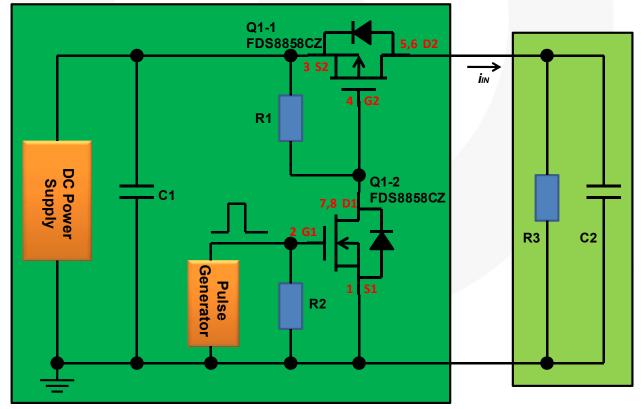


Figure 16. Startup Test Circuit - without FR011L5J

Typical Application Waveforms

Typical USB3.0 conditions.

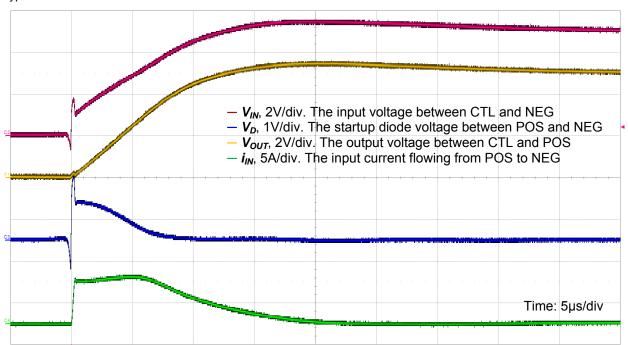


Figure 17. Normal Bias Startup Waveform, DC Power Source=5V, C_1 =100 μ F, C_2 =10 μ F, R_1 = R_2 =10k Ω , R_3 =27 Ω

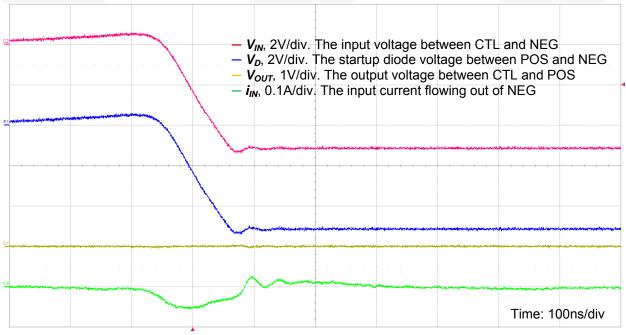


Figure 18. Reverse Bias Startup Waveform, DC Power Source=5V, C₁=100μF, C₂=10μF, R₁=R₂=10kΩ, R₃=27Ω

Typical Application Waveforms (Continued)

Typical USB3.0 conditions.

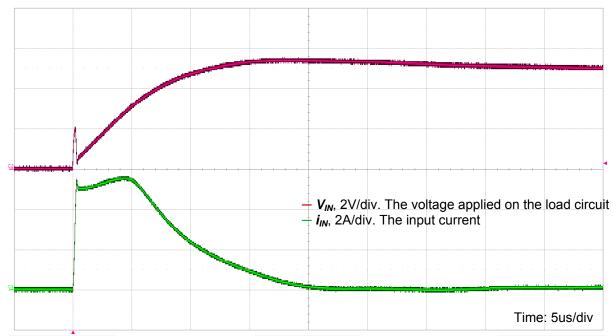


Figure 19. Startup Waveform without FR011L5J, DC Power Source=5V, C_1 =100 μ F, C_2 =10uF, R_1 = R_2 =10 $k\Omega$, R_3 =27 Ω

Application Information

Figure 17 shows the voltage and current waveforms when a virtual USB3.0 device is connected to a 5V source. A USB application allows a maximum source output capacitance of C_1 = 120 μ F and a maximum device-side input capacitance of C_2 = 10 μ F plus a maximum load (minimum resistance) of R_3 = 27 Ω . C_1 = 100 μ F, C_2 = 10 μ F and R_3 = 27 Ω were used for testing.

When the DC power source is connected to the circuit (refer to Figure 13), the built-in startup diode initially conducts the current such that the USB device powers up. Due to the initial diode voltage drop, the FR011L5J effectively reduces the peak inrush current of a hot plug event. Under these test conditions, the input inrush current reaches about 6.3A peak. While the current flows, the input voltage increases. The speed of this input voltage increase depends on the time constant formed by the load resistance R_3 and load capacitance C_2 . The larger the time constant, the slower the input voltage increase. As the input voltage approaches a level equal to the protector's turn-on voltage, V_{ON} , the protector turns on and operates in Low-Resistance Mode as defined by V_{IN} and operating current I_{IN} .

In the event of a negative transient, or when the DC power source is reversely connected to the circuit, the device blocks the flow of current and holds off the voltage, thereby protecting the USB device. Figure 18 shows the voltage and current waveforms when a virtual

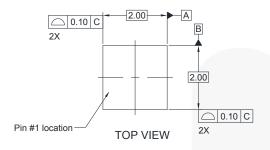
USB3.0 device is reversely biased; the output voltage is near 0 and response time is less than 50ns.

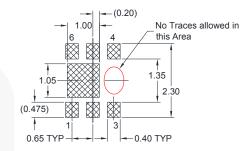
Figure 19 shows the voltage and current waveforms when no reverse bias protection is implemented. In Figure 17, while the reverse bias protector is present, the input voltage, V_{IN} , and the output voltage, V_{O} , are separated and look different. When this reverse bias protector is removed, V_{IN} and V_{O} merge, as shown inFigure 19 as V_{IN} . This V_{IN} is also the voltage applied to the load circuit. It can be seen that, with reverse bias protection, the voltage applied to the load and the current flowing into the load look very much the same as without reverse bias protection.

Benefits of Reverse Bias Protection

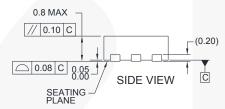
The most important benefit is to prevent accidently reverse-biased voltage from damaging the USB load. Another benefit is that the peak startup inrush current can be reduced. How fast the input voltage rises, the input/output capacitance, the input voltage, and how heavy the load is determine how much the inrush current can be reduced. In a 5V USB application, for example, the inrush current can be 5% - 20% less with different input voltage rising rate and other factors. This can offer a system designer the option of increasing C_2 while keeping "effective" USB device capacitance down.

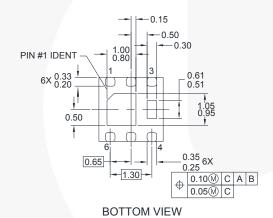
Physical Dimensions

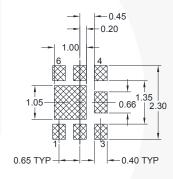




RECOMMENDED LAND PATTERN OPT 1







RECOMMENDED LAND PATTERN OPT 2

NOTES:

- A. DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-229 DATED AUG/2003
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
- D. DRAWING FILENAME: MKT-MLP06Lrev3.

Figure 20. 6-Lead, Molded Leadless Package (MLP), Dual, Non-JEDEC, 2mm Square, Single-Tied DAP

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings: http://www.fairchildsemi.com/packaging/.





TRADEMARKS

Build it Now™

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

F-PFS™ FRFET® AccuPower™ Global Power ResourceSM AX-CAP™* GreenBridae™ BitSiC™

Green FPS™

Green FPS™ e-Series™ CorePLUS™ CorePOWER™ Gmax™ GTO™ CROSSVOLT™ IntelliMAX™ CTL™

ISOPLANAR™ Current Transfer Logic™ Making Small Speakers Sound Louder DEUXPEED®

and Better™ Dual Cool™ EcoSPARK® MegaBuck™ MIČROCOUPLER™ EfficientMax™ ESBC™ MicroFET™

MicroPak™ MicroPak2™ Fairchild® MillerDrive™ Fairchild Semiconductor® MotionMax™ FACT Quiet Series™ mWSaver™ FACT[®] OptoHiT™ FAST® OPTOLOGIC® FastvCore™ OPTOPLANAR®

FETBench™ FlashWriter® **FPSTM**

PowerTrench® PowerXS™

Programmable Active Droop™

QFET QS™ Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™ SignalWise™

SmartMax™ SMART START™

Solutions for Your Success™

STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SyncFET™ Sync-Lock™ SYSTEM GENERAL®. The Power Franchise®

puwer TinyBoost™ TinyBuck™ TinyCalc™ TinyLogic[®] TINYOPTO™ TinyPower™ TinyPWM™ TinyWire™ TranSiC™ TriFault Detect™ TRUECURRENT®* uSerDes™

UHC Ultra FRFET™ UniFET™ VCX^{TM} VisualMax™ VoltagePlus™ XST

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com,

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms				
Datasheet Identification	Product Status	Definition		
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.		

Rev. 162

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for ESD Suppressors / TVS Diodes category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

60KS200C D12V0H1U2WS-7 D18V0L1B2LP-7B 82356050220 D5V0M5U6V-7 NTE4902 P4KE27CA P6KE11CA P6KE39CA-TP
P6KE8.2A SA110CA SA60CA SA64CA SMBJ12CATR SMBJ8.0A SMLJ30CA-TP ESD101-B1-02ELS E6327 ESD112-B1-02EL E6327
ESD119B1W01005E6327XTSA1 ESD5V0J4-TP ESD5V0L1B02VH6327XTSA1 ESD7451N2T5G 19180-510 CPDT-5V0USP-HF
3.0SMCJ33CA-F 3.0SMCJ36A-F HSPC16701B02TP D3V3Q1B2DLP3-7 D55V0M1B2WS-7 DESD5V0U1BL-7B DRTR5V0U4SL-7
SCM1293A-04SO ESD200-B1-CSP0201 E6327 ESD203-B1-02EL E6327 SM12-7 SMF8.0A-TP SMLJ45CA-TP CEN955 W/DATA
82350120560 82356240030 VESD12A1A-HD1-GS08 CPDUR5V0R-HF CPDUR24V-HF CPDQC5V0U-HF CPDQC5V0USP-HF
CPDQC5V0-HF D1213A-01LP4-7B D1213A-02WL-7 ESDLIN1524BJ-HQ 5KP100A